

GP1S094HCZ0F

Gap: 3mm, Slit: 0.3mm **Phototransistor Output, Compact Transmissive Photointerrupter**

■ Description

GP1S094HCZ0F is a compact-package, phototransistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides non-contact sensing. The compact package series is a result of unique technology combing transfer and injection molding.

This device has a wide gap and positioning pins.

■ Features

- 1. Transmissive with phototransistor output
- 2. Highlights:
 - Compact Size
 - Positioning Pin to prevent misalignment
- 3. Key Parameters:
 - · Gap Width: 3mm
 - · Slit Width (detector side): 0.3mm
 - Package : 5.5×2.6×4.8mm
- 4. Lead free and RoHS directive compliant

■ Agency approvals/Compliance

1. Compliant with RoHS directive

■ Applications

- 1. Detection of object presence or motion.
- 2. Example: printer, lens control for camera

Notice The content of data sheet is subject to change without prior notice.

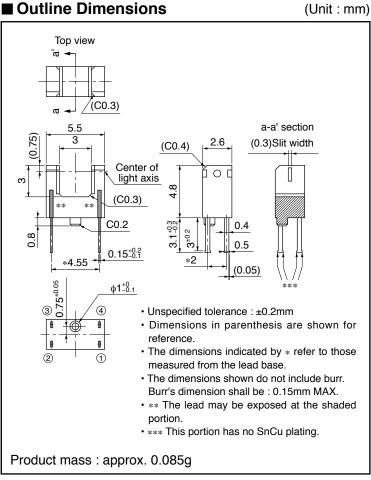
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■ Internal Connection Diagram

Top view 20 ① Anode 2 Collector 3 Emitter 4 Cathode

■ Outline Dimensions

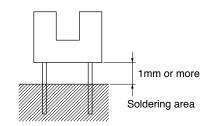


Plating material: SnCu (Cu: TYP. 2%)

Country of origin Japan



■ Absolute Maximum Ratings					
	Parameter	Symbol	Rating	Unit	
	Forward current	I_F	50	mA	
Input	Reverse voltage	V_R	6	V	
	Power dissipation	P	75	mW	
Output	Collector-emitter voltage	V_{CEO}	35	V	
	Emitter-collector voltage	V _{ECO}	6	V	
	Collector current	$I_{\rm C}$	20	mA	
	Collector power dissipation	P _C	75	mW	
Total j	power dissipation	P _{tot}	100	mW	
Operating temperature		Topr	-25 to +85	°C	
Storage temperature		T _{stg}	-40 to +100	°C	
*1Solder	ring temperature	T _{sol}	260	°C	



■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

								<u> </u>
	Parameter		Symbol	Condition	MIN.	TYP.	MAX.	Unit
Forward voltage		V_F	$I_F=20mA$	_	1.2	1.4	V	
Input	Reverse current		I_R	$V_R=3V$	-	-	10	μΑ
Output	Collector dark current		I_{CEO}	$V_{CE}=20V$	_	_	100	nA
Collector curren	Collector current		I_{C}	$V_{CE}=5V$, $I_F=5mA$	40	-	400	μΑ
Transfer charac-	Collector-emitter saturation voltage	voltage	V _{CE(sat)}	$I_F=10mA, I_C=40\mu A$	_	_	0.4	V
	Response time	Rise time	t _r	$V_{CE}\text{=}5V,I_{C}\text{=}100\mu\text{A},R_{L}\text{=}1\text{k}\Omega$	_	50	150	μs
		Fall time	$t_{\rm f}$		_	50	150	μs

^{*1} For 5s or less



Fig.1 Forward Current vs.

Ambient Temperature

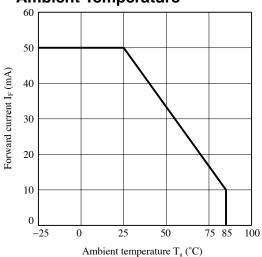


Fig.3 Forward Current vs. Forward Voltage

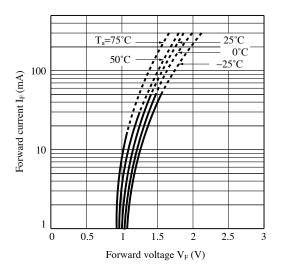


Fig.5 Collector Current vs.
Collector-emitter Voltage

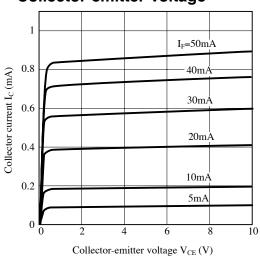


Fig.2 Power Dissipation vs. Ambient Temperature

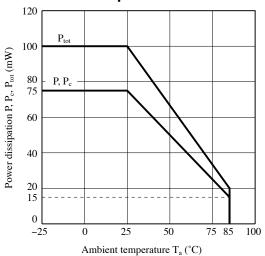


Fig.4 Collector Current vs. Forward Current

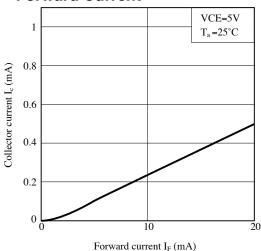


Fig.6 Relative Collector Current vs.
Ambient Temperature

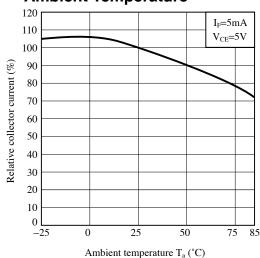




Fig.7 Collector-emitter Saturation Voltage vs. Ambient Temperature

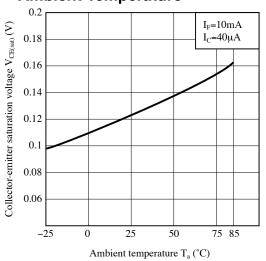


Fig.8 Collector Dark Current vs.
Ambient Temperature

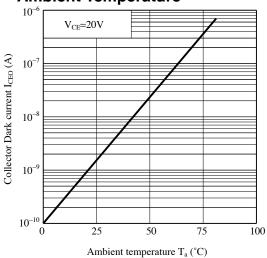


Fig.9 Response Time vs. Load Resistance

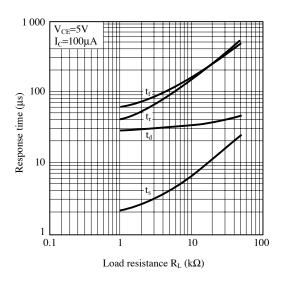


Fig.10 Test Circuit for Response Time

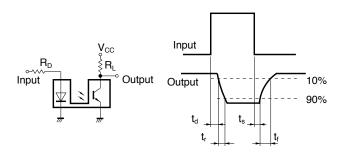


Fig.11 Detecting Position Characteristics (1)

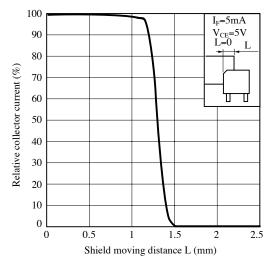
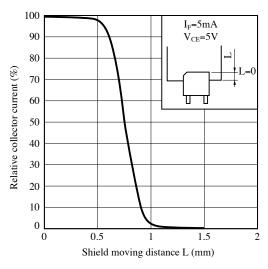


Fig.12 Detecting Position Characteristics (2)



Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



■ Design Considerations

Design guide

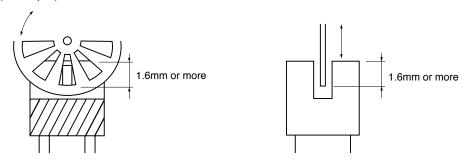
1) Prevention of detection error

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board

Opaque board shall be installed at place 1.6mm or more from the top of elements.

(Example)



This product is not designed against irradiation and incorporates non-coherent IRED.

Degradation

In general, the emission of the IRED used in photointerrupter will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

Parts

This product is assembled using the below parts.

• Photodetector (qty.: 1)

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (μs)
Phototransistor	Silicon (Si)	930	700 to 1 200	20

• Photo emitter (qty.: 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3

Material

Case	Lead frame	Lead frame plating
Black polyphernylene sulfide resin (UL94 V-0)	42Alloy	SnCu plating



■ Manufacturing Guidelines

Soldering Method

Flow Soldering:

Soldering should be completed below 260°C and within 5 s.

Please solder within one time.

Soldering area is 1mm or more away from the bottom of housing.

Please take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

Hand soldering

Hand soldering should be completed within 3 s when the point of solder iron is below 350°C.

Please solder within one time.

Please don't touch the terminals directly by soldering iron.

Soldered product shall treat at normal temperature.

Other notice

Please take care not to let any external force exert on lead pins.

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the cooling and soldering conditions.

Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning:

Do not execute ultrasonic cleaning.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



■ Package specification

● Sleeve package

Package materials

Sleeve : Polyphernylene Stopper : Styrene-Elastomer

Package method

MAX. 100 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves in one case.



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 - --- Telecommunication equipment [terminal]
 - --- Test and measurement equipment
 - --- Industrial control
 - --- Audio visual equipment
 - --- Consumer electronics
- (ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection

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